

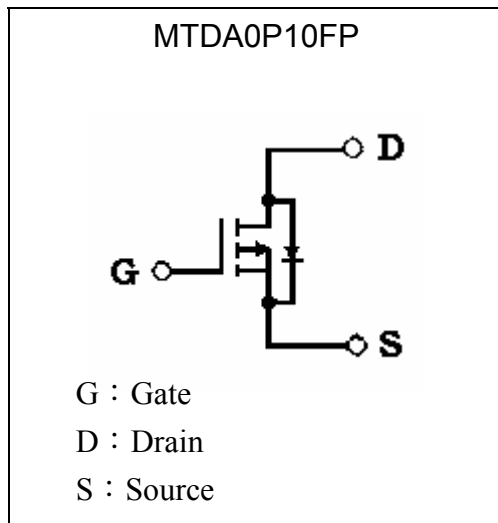
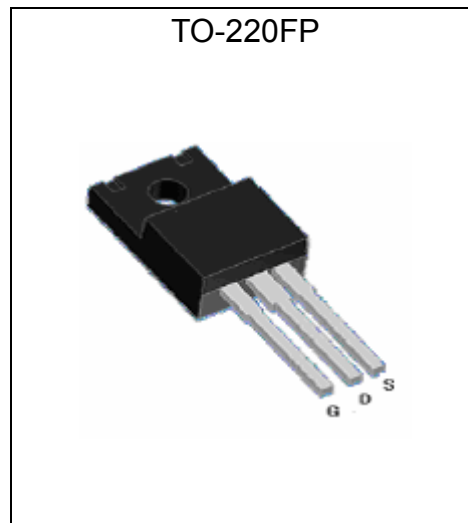
P-Channel Logic Level Enhancement Mode Power MOSFET

MTDA0P10FP

BV_{DSS}	-100V
I_D	-22A
$R_{DS(on)(MAX)}$	120m Ω

Features

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating package

Equivalent Circuit

Outline

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current @ $T_c=25^\circ\text{C}$	I_D	-22	A
Continuous Drain Current @ $T_c=100^\circ\text{C}$	I_D	-15	
Pulsed Drain Current *1	I_{DM}	-75	
Avalanche Current	I_{AS}	-15	
Avalanche Energy @ $L=0.1\text{mH}$, $I_D=-15\text{A}$, $R_G=25\Omega$	E_{AS}	22.5	mJ
Repetitive Avalanche Energy @ $L=0.05\text{mH}$ *2	E_{AR}	11.25	
Total Power Dissipation @ $T_c=25^\circ\text{C}$	P_d	62	W
Total Power Dissipation @ $T_c=100^\circ\text{C}$		31	
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55~+175	$^\circ\text{C}$

Note : *1. Pulse width limited by maximum junction temperature

 *2. Duty cycle $\leq 1\%$



Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	2.42	°C/W
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	62.5	°C/W

Characteristics (Tc=25°C, unless otherwise specified)

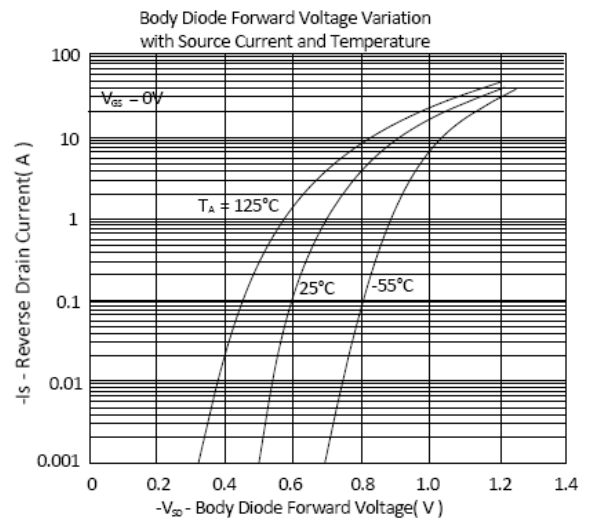
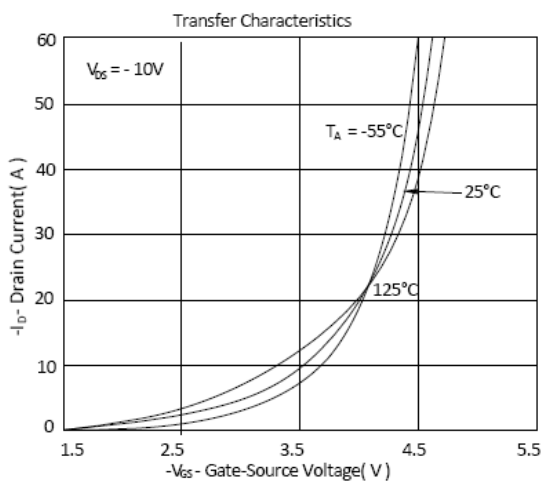
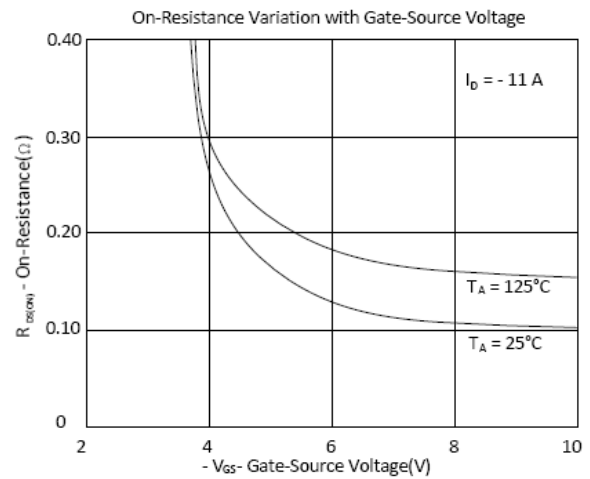
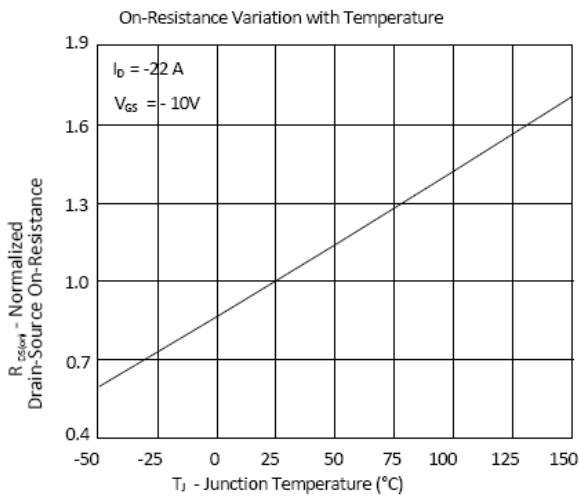
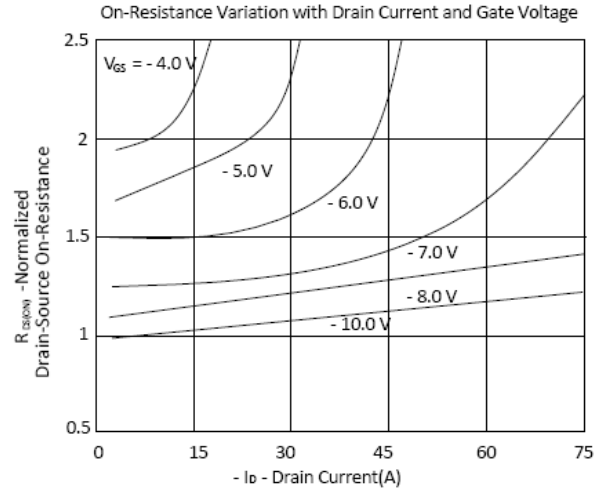
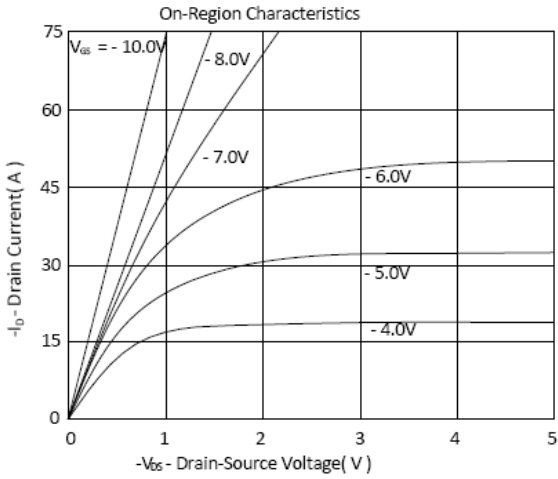
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-100	-	-	V	$V_{GS}=0, I_D=-250\mu A$
$V_{GS(th)}$	-1.5	-2.5	-4.0	V	$V_{DS}=V_{GS}, I_D=-250\mu A$
I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20, V_{DS}=0$
I_{DSS}	-	-	-1	μA	$V_{DS}=-80V, V_{GS}=0$
	-	-	-25		$V_{DS}=-70V, V_{GS}=0, T_J=125^\circ C$
$I_{D(ON)} *1$	-22	-	-	A	$V_{DS}=-5V, V_{GS}=-10V$
$R_{DS(ON)} *1$	-	105	120	mΩ	$V_{GS}=-10V, I_D=-11A$
$G_{FS} *1$	-	8	-	S	$V_{DS}=-5V, I_D=-11A$
Dynamic					
$Q_g *1, 2$	-	58	-	nC	$I_D=-11A, V_{DS}=-80V, V_{GS}=-10V$
$Q_{gs} *1, 2$	-	13.8	-		
$Q_{gd} *1, 2$	-	10.5	-		
$t_{d(ON)} *1, 2$	-	15	-	ns	$V_{DS}=-10V, I_D=-1A, V_{GS}=-10V, R_G=6\Omega$
$t_r *1, 2$	-	67	-		
$t_{d(OFF)} *1, 2$	-	50	-		
$t_f *1, 2$	-	50	-	pF	$V_{GS}=0V, V_{DS}=-25V, f=1MHz$
C_{iss}	-	7760	-		
C_{oss}	-	1683	-		
C_{rss}	-	1643	-	Ω	$V_{GS}=15mV, V_{DS}=0, f=1MHz$
R_g	-	4.5	-		
Source-Drain Diode					
$I_S *1$	-	-	-22	A	
$I_{SM} *3$	-	-	-75		
$V_{SD} *1$	-	-	-1.3	V	$I_F=I_S, V_{GS}=0V$
t_{rr}	-	150	-	ns	$I_F=-5A, dI_F/dt=100A/\mu s$
Q_{rr}	-	830	-	nC	

Note : *1.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

Ordering Information

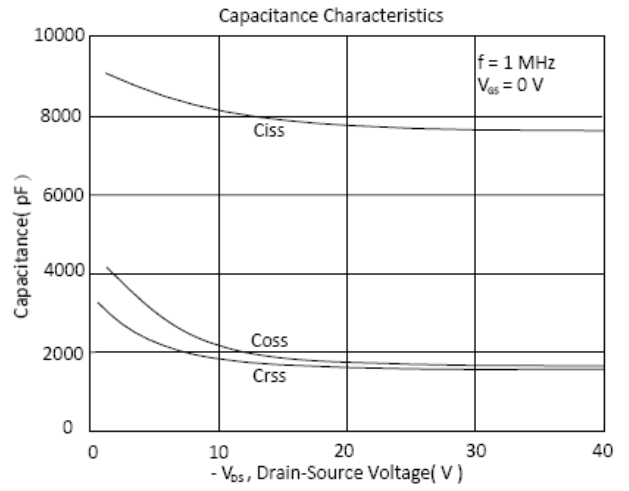
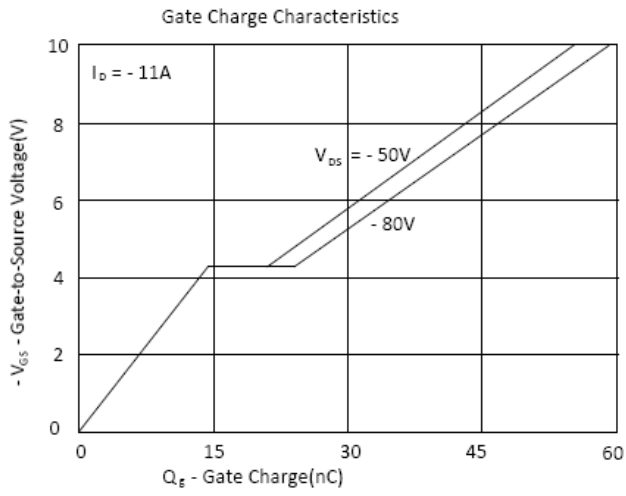
Device	Package	Shipping
MTDA0P10FP	TO-220FP (Pb-free lead plating package)	50 pcs / tube, 20 tubes/box, 4 boxes/carton

Typical Characteristics





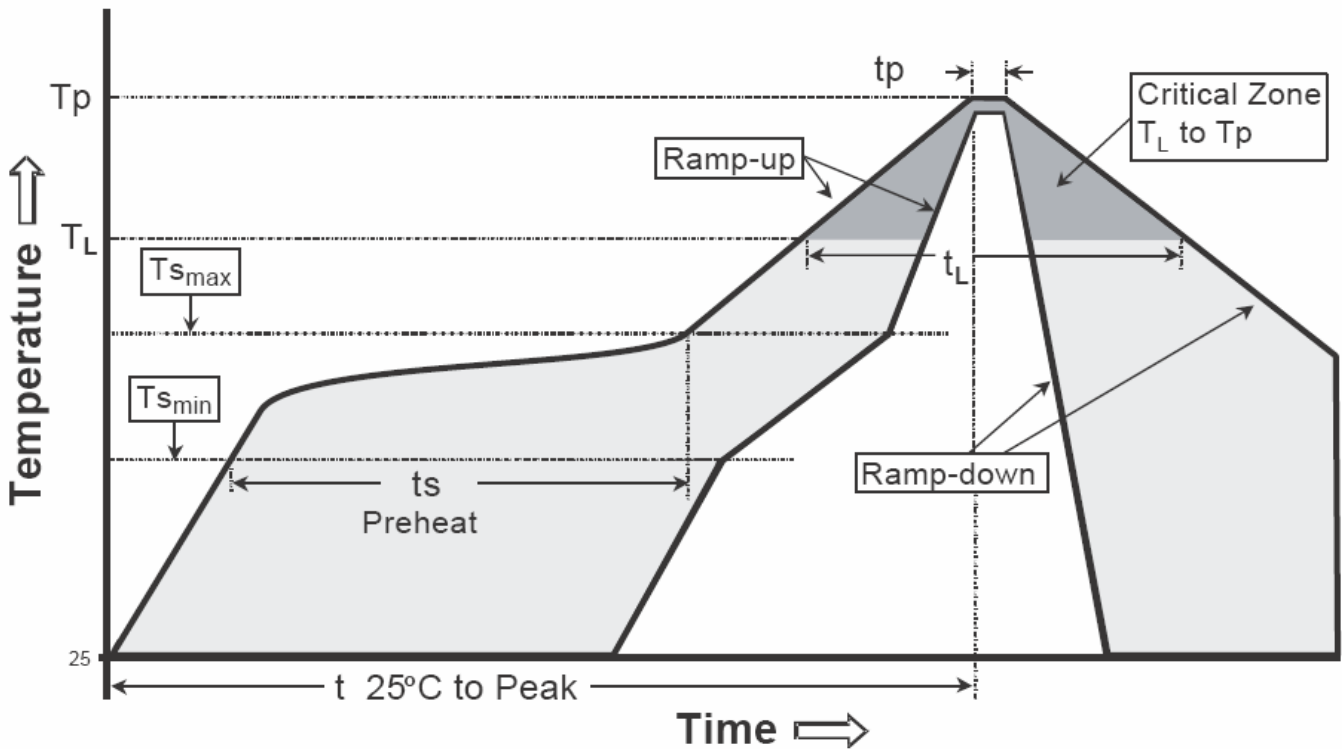
Typical Characteristics(Cont.)



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

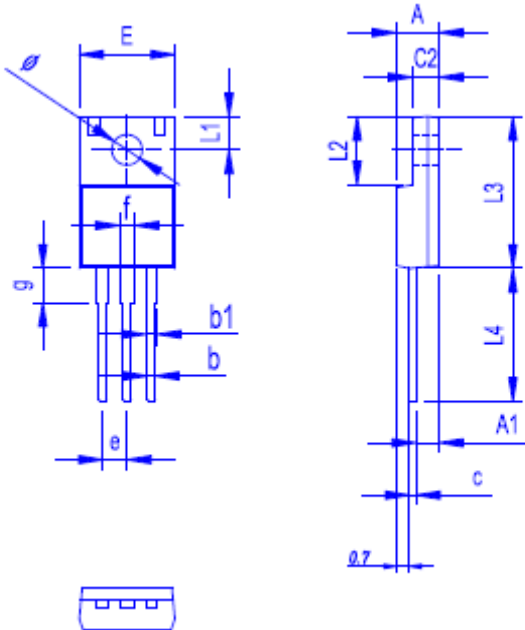
Recommended temperature profile for IR reflow



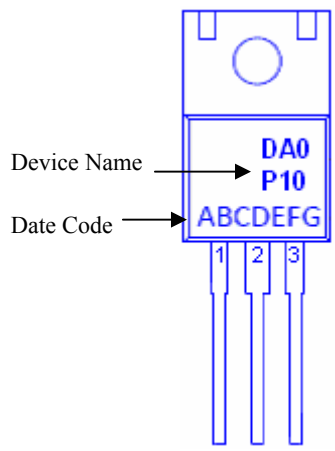
Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{Smax} to T _P)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{S min})	100°C	150°C
-Temperature Max(T _{S max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t _p)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-220FP Dimension



Marking:



Device Name → **DA0
P10**

Date Code → **ABCDEFG**

1 2 3

Style: Pin 1.Gate 2.Drain 3.Source

3-Lead TO-220FP Plastic Package
CYStek Package Code: FP

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1654	0.1890	4.20	4.80	L2	0.2717	0.2953	6.90	7.50
A1	0.0768	0.1122	1.95	2.85	L3	0.6181	0.6417	15.70	16.30
b	0.0256	0.0413	0.65	1.05	L4	0.5315	0.5709	13.50	14.50
b1	0.0354	0.0591	0.90	1.50	Φ	0.1181	0.1339	3.00	3.40
c	0.0217	0.0315	0.55	0.80	e	0.0925	0.1083	2.35	2.75
c2	0.0984	0.1220	2.50	3.10	f	0.0512	0.0748	1.30	1.90
E	0.3819	0.4055	9.70	10.30	g	0.1339	0.1496	3.40	3.80
L1	0.1260	0.1496	3.20	3.80					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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